

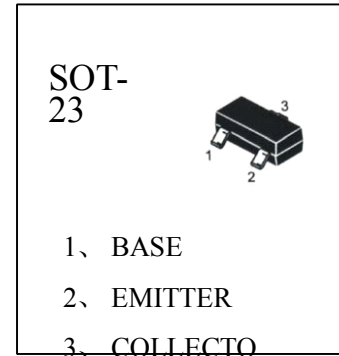
SOT-23 Plastic –Encapsulate Transistors

FEATURES

Power dissipation

MARKING : C1815=HF

MAXIMUM RATINGS (TA=25°C unless otherwise noted)



Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	60	V
VCEO	Collector-Emitter Voltage	50	V
VEBO	Emitter-Base Voltage	5	V
IC	Collector Current -Continuous	150	mA
PC	Collector Power Dissipation	200	mW
Tj	Junction Temperature	125	°C
Tstg	Storage Temperature	-55-125	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC= 100uA, IE=0	60			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 0.1mA, IB=0	50			V
Collector cut-off current	ICBO	VCB=60 V, IE=0			0.1	A
Collector cut-off current	ICEO	VCE=50V, IB=0			0.1	uA
Emitter cut-off current	IEBO	VEB= 5V, IC=0			0.1	uA
DC current gain	hFE	VCE= 6V, IC= 2mA	130		400	
Collector-emitter saturation voltage	VCE(sat)	IC=100mA, IB= 10mA			0.25	V
Base-emitter saturation voltage	VBE(sat)	IC=100mA, IB= 10mA			1	V
Transition frequency	fT	VCE=10V, IC= 1mA, f=30MHz	80			MHz

CLASSIFICATION OF hFE

Rank	L	H
Range	130-200	200-400

Typical Characteristics

C1815

